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# FDMT800120DC

## N-Channel Dual Cool™ 88 PowerTrench® MOSFET

120 V, 128 A, 4.2 mΩ

### Features

- Max  $r_{DS(on)}$  = 4.2 mΩ at  $V_{GS} = 10$  V,  $I_D = 20$  A
- Max  $r_{DS(on)}$  = 6.4 mΩ at  $V_{GS} = 6$  V,  $I_D = 16$  A
- Advanced Package and Silicon combination for low  $r_{DS(on)}$  and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- Low profile 8x8mm MLP package
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

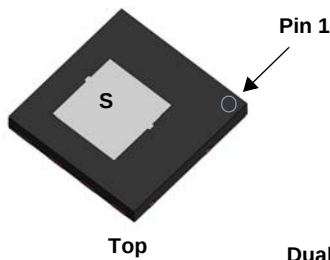


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process. Advancements in both silicon and Dual Cool™ package technologies have been combined to offer the lowest  $r_{DS(on)}$  while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance.

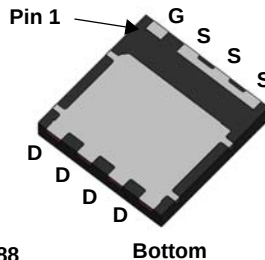
### Applications

- OringFET / Load Switching
- Synchronous Rectification
- DC-DC Conversion

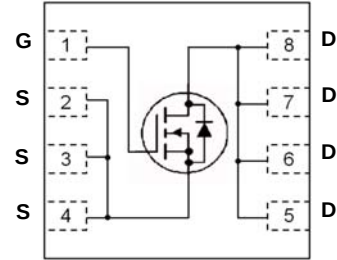


Top

Dual Cool™ 88



Bottom



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                   | Ratings     | Units |
|----------------|-------------------------------------------------------------|-------------|-------|
| $V_{DS}$       | Drain to Source Voltage                                     | 120         | V     |
| $V_{GS}$       | Gate to Source Voltage                                      | ±20         | V     |
| $I_D$          | Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 5) | 128         | A     |
|                | -Continuous $T_C = 100^\circ\text{C}$ (Note 5)              | 81          |       |
|                | -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)              | 20          |       |
|                | -Pulsed (Note 4)                                            | 767         |       |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)                      | 1350        | mJ    |
| $P_D$          | Power Dissipation $T_C = 25^\circ\text{C}$                  | 156         | W     |
|                | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)        | 3.2         |       |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range            | -55 to +150 | °C    |

### Thermal Characteristics

|                 |                                                     |     |      |
|-----------------|-----------------------------------------------------|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Top Source)   | 1.6 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Bottom Drain) | 0.8 |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a)   | 38  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1b)   | 81  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1i)   | 15  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1j)   | 21  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1k)   | 9   |      |

### Package Marking and Ordering Information

| Device Marking | Device       | Package       | Reel Size | Tape Width | Quantity   |
|----------------|--------------|---------------|-----------|------------|------------|
| 800120DC       | FDMT800120DC | Dual Cool™ 88 | 13"       | 13.3 mm    | 3000 units |

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

**Off Characteristics**

|                                      |                                           |                                                                             |     |    |     |                        |
|--------------------------------------|-------------------------------------------|-----------------------------------------------------------------------------|-----|----|-----|------------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$                      | 120 |    |     | V                      |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$ |     | 97 |     | mV/ $^{\circ}\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 96\text{ V}$ , $V_{GS} = 0\text{ V}$                              |     |    | 1   | $\mu\text{A}$          |
| $I_{GSS}$                            | Gate to Source Leakage Current            | $V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$                          |     |    | 100 | nA                     |

**On Characteristics**

|                                        |                                                          |                                                                                    |     |      |     |                        |
|----------------------------------------|----------------------------------------------------------|------------------------------------------------------------------------------------|-----|------|-----|------------------------|
| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$                                 | 2.0 | 3.1  | 4.0 | V                      |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$        |     | -12  |     | mV/ $^{\circ}\text{C}$ |
| $r_{DS(on)}$                           | Static Drain to Source On Resistance                     | $V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$                                       |     | 3.45 | 4.2 | m $\Omega$             |
|                                        |                                                          | $V_{GS} = 6\text{ V}$ , $I_D = 16\text{ A}$                                        |     | 4.6  | 6.4 |                        |
|                                        |                                                          | $V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$ |     | 6.3  | 7.7 |                        |
| $g_{FS}$                               | Forward Transconductance                                 | $V_{DS} = 5\text{ V}$ , $I_D = 20\text{ A}$                                        |     | 69   |     | S                      |

**Dynamic Characteristics**

|           |                              |                                                                        |     |      |      |          |
|-----------|------------------------------|------------------------------------------------------------------------|-----|------|------|----------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ ,<br>$f = 1\text{ MHz}$ |     | 5605 | 7850 | pF       |
| $C_{oss}$ | Output Capacitance           |                                                                        |     | 778  | 1090 | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                        |     | 27   | 40   | pF       |
| $R_g$     | Gate Resistance              |                                                                        | 0.1 | 1.4  | 3.5  | $\Omega$ |

**Switching Characteristics**

|              |                               |                                                                                                        |                                                 |     |     |    |
|--------------|-------------------------------|--------------------------------------------------------------------------------------------------------|-------------------------------------------------|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time            | $V_{DD} = 60\text{ V}$ , $I_D = 20\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$ |                                                 | 29  | 47  | ns |
| $t_r$        | Rise Time                     |                                                                                                        |                                                 | 18  | 33  | ns |
| $t_{d(off)}$ | Turn-Off Delay Time           |                                                                                                        |                                                 | 40  | 64  | ns |
| $t_f$        | Fall Time                     |                                                                                                        |                                                 | 9.5 | 19  | ns |
| $Q_{g(TOT)}$ | Total Gate Charge             | $V_{GS} = 0\text{ V to }10\text{ V}$                                                                   | $V_{DD} = 60\text{ V}$ ,<br>$I_D = 20\text{ A}$ | 76  | 107 | nC |
| $Q_{g(TOT)}$ | Total Gate Charge             | $V_{GS} = 0\text{ V to }6\text{ V}$                                                                    |                                                 | 48  | 68  | nC |
| $Q_{gs}$     | Gate to Source Charge         |                                                                                                        |                                                 | 25  |     | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |                                                                                                        |                                                 | 15  |     | nC |

**Drain-Source Diode Characteristics**

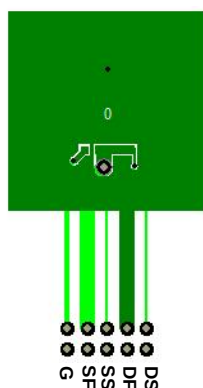
|          |                                       |                                                          |  |     |     |    |
|----------|---------------------------------------|----------------------------------------------------------|--|-----|-----|----|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}$ , $I_S = 2.9\text{ A}$ (Note 2)    |  | 0.7 | 1.1 | V  |
|          |                                       | $V_{GS} = 0\text{ V}$ , $I_S = 20\text{ A}$ (Note 2)     |  | 0.8 | 1.2 |    |
| $t_{rr}$ | Reverse Recovery Time                 | $I_F = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ |  | 87  | 139 | ns |
| $Q_{rr}$ | Reverse Recovery Charge               |                                                          |  | 164 | 263 | nC |

## Thermal Characteristics

|                 |                                                     |     |      |
|-----------------|-----------------------------------------------------|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Top Source)   | 1.6 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Bottom Drain) | 0.8 |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a)   | 38  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1b)   | 81  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1c)   | 26  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1d)   | 34  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1e)   | 14  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1f)   | 16  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1g)   | 26  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1h)   | 60  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1i)   | 15  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1j)   | 21  |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1k)   | 9   |      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1l)   | 11  |      |

### NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below.  $R_{\theta CA}$  is determined by the user's board design.



a. 38 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 81 °C/W when mounted on a minimum pad of 2 oz copper

- c. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in² pad of 2 oz copper
- d. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
- e. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in² pad of 2 oz copper
- f. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
- g. 200FPM Airflow, No Heat Sink, 1 in² pad of 2 oz copper
- h. 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
- i. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in² pad of 2 oz copper
- j. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
- k. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in² pad of 2 oz copper
- l. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu$ s, Duty cycle < 2.0%.

3.  $E_{AS}$  of 1350 mJ is based on starting  $T_J = 25$  °C; N-ch:  $L = 3$  mH,  $I_{AS} = 30$  A,  $V_{DD} = 120$  V,  $V_{GS} = 10$  V. 100% test at  $L = 0.1$  mH,  $I_{AS} = 93$  A.

4. Pulsed Id please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

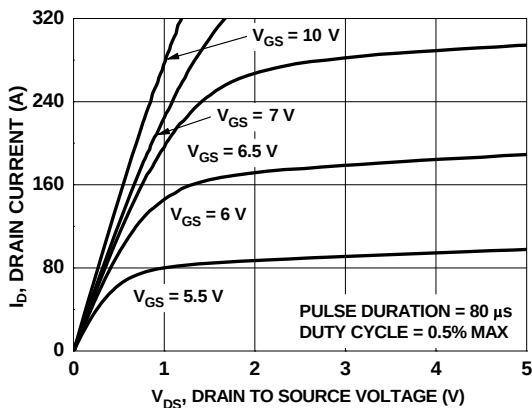


Figure 1. On-Region Characteristics

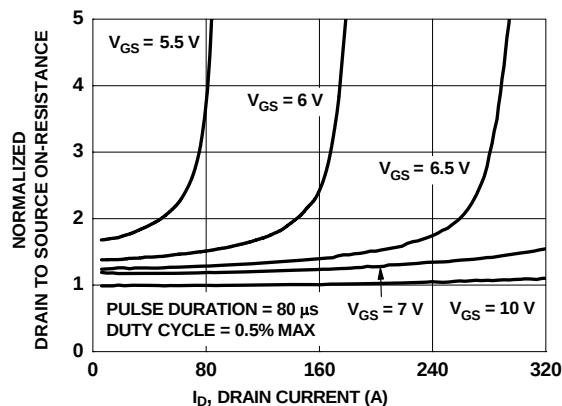


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

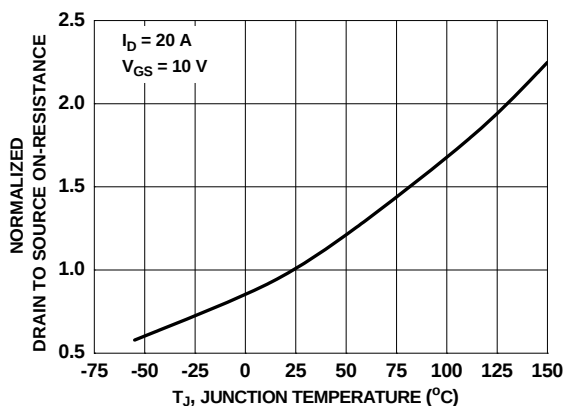


Figure 3. Normalized On-Resistance vs Junction Temperature

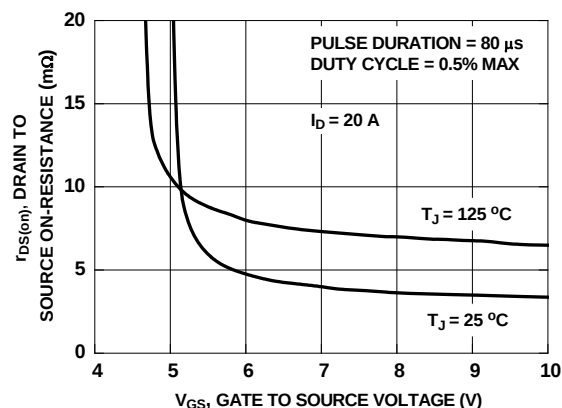


Figure 4. On-Resistance vs Gate to Source Voltage

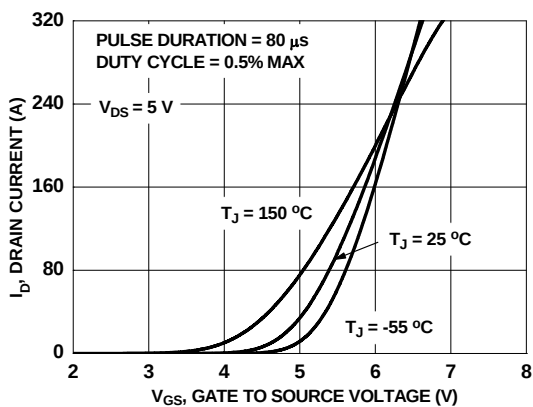


Figure 5. Transfer Characteristics

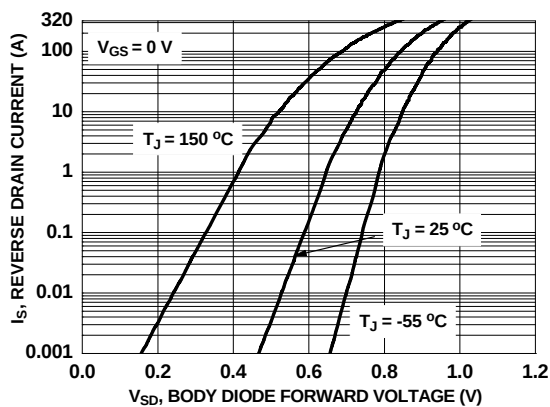


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

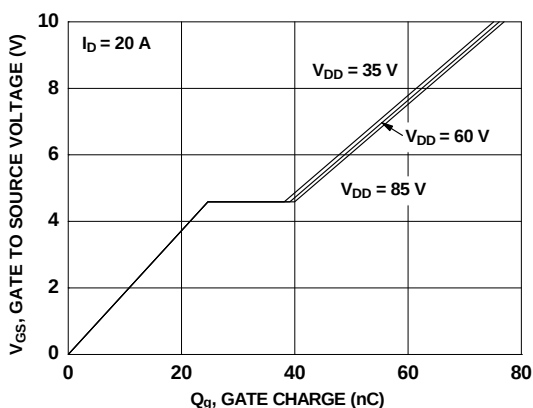


Figure 7. Gate Charge Characteristics

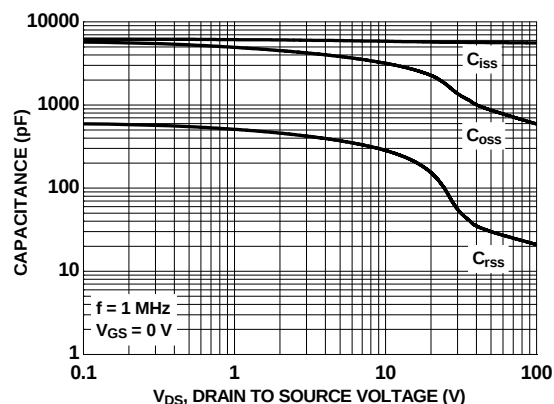


Figure 8. Capacitance vs Drain to Source Voltage

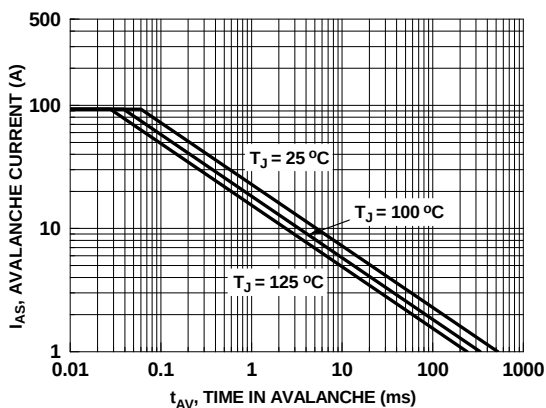


Figure 9. Unclamped Inductive Switching Capability

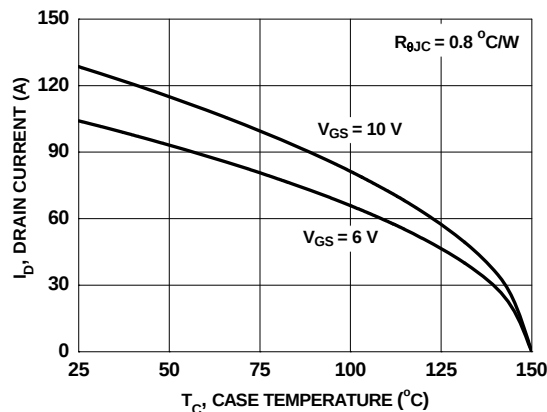


Figure 10. Maximum Continuous Drain Current vs Case Temperature

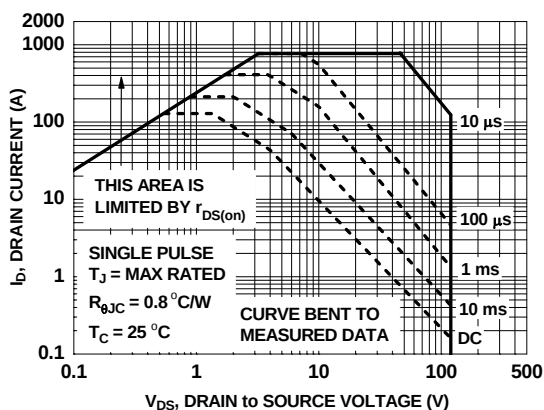


Figure 11. Forward Bias Safe Operating Area

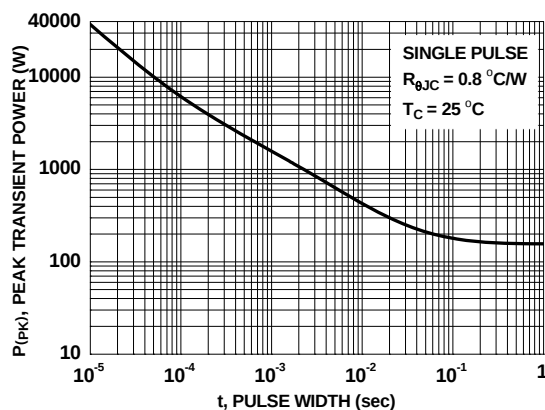
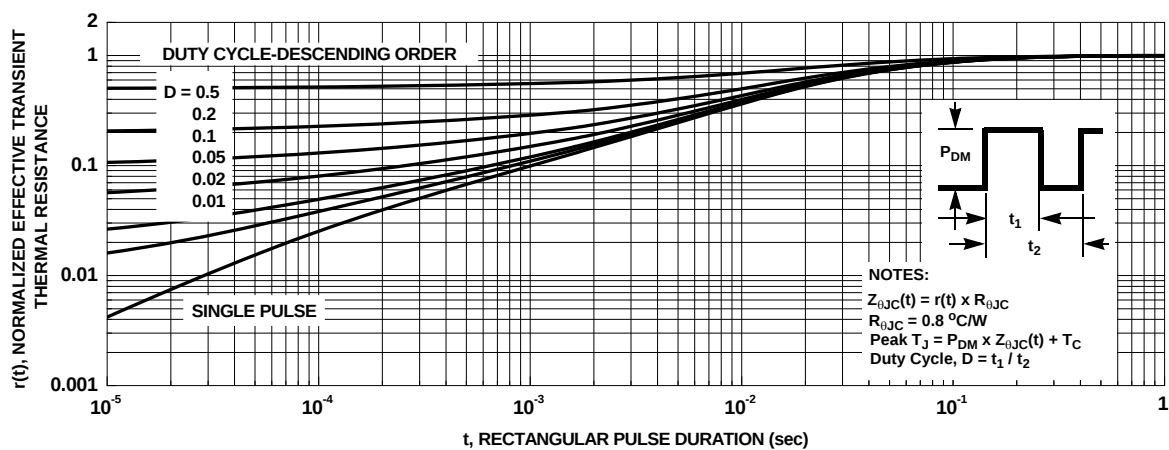
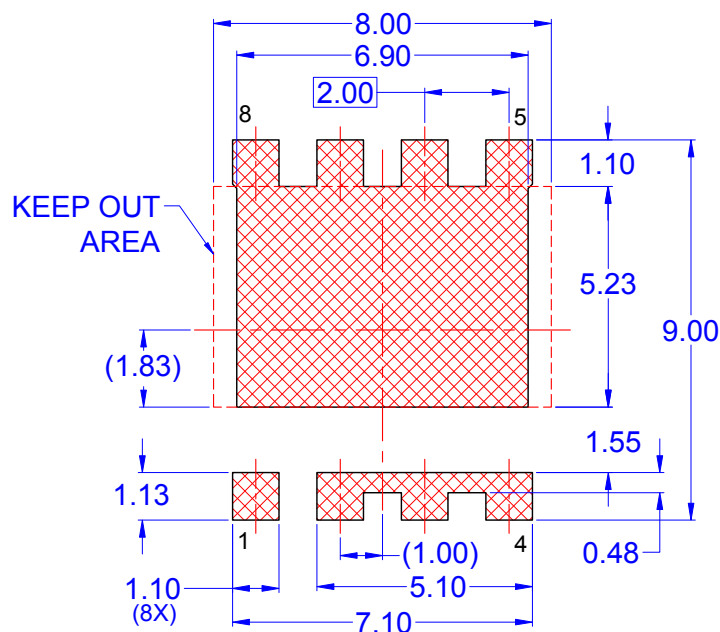
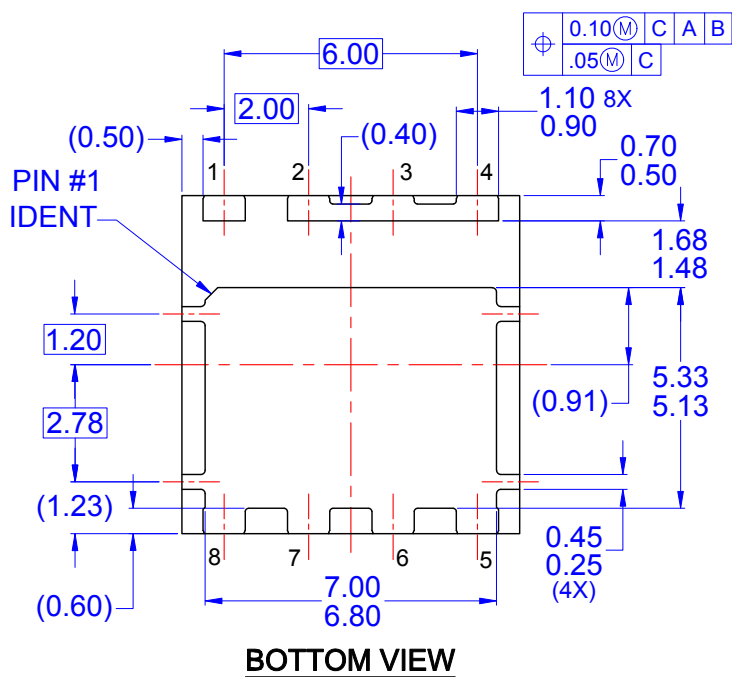
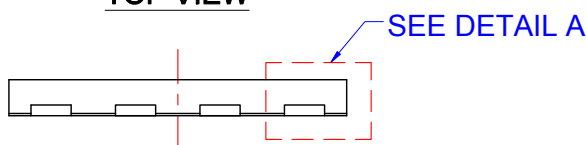
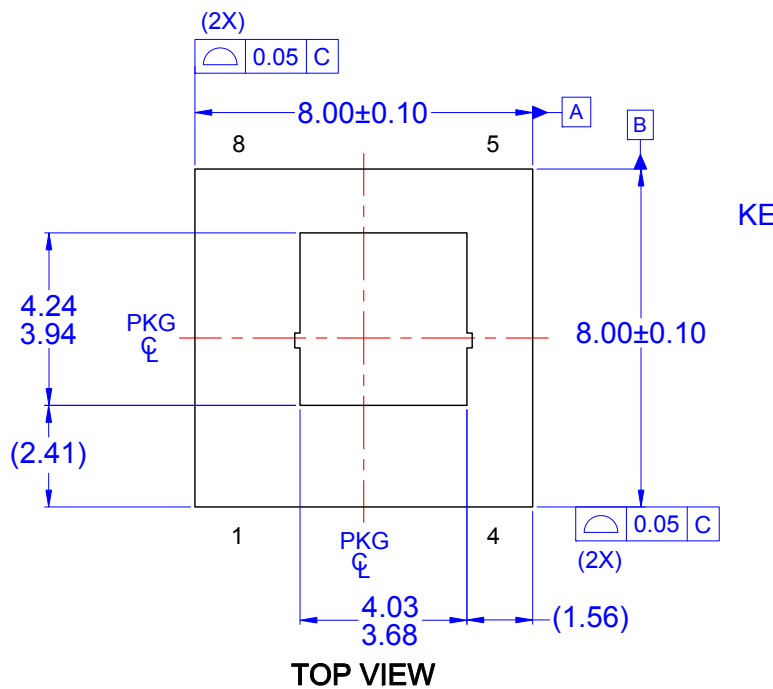


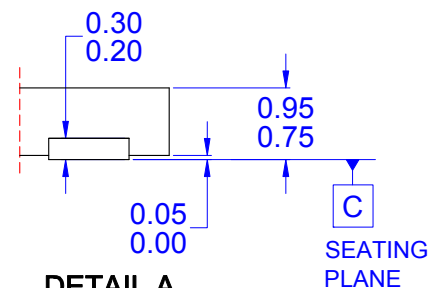
Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted





LAND PATTERN RECOMMENDATION



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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9